

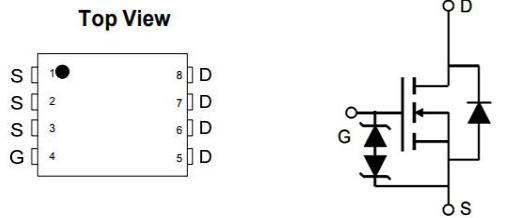
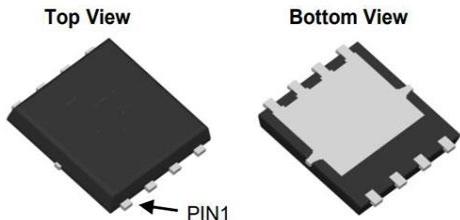
**30V /34A Single N Power MOSFET**
**General Description**

30V /34A Single N Power MOSFET

Very low on-resistance RDS(on) @ VGS=4.5 V

Pb-free lead plating; RoHS compliant

<b>V<sub>DS</sub></b>	30	V
<b>R<sub>DS(on),TYP@VGS=10V</sub></b>	3.6	mΩ
<b>R<sub>DS(on),TYP@VGS=4.5</sub></b>	5.7	mΩ
<b>I<sub>D</sub></b>	34	A



Part ID	Package Type	Marking	Tape and reel infomation
SM6366ED1RL	DFN5x6	6366	3000


 100% UIS Tested  
100% RG Tested

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	20	±V
Continuous Drain Current A TA=25°C	I <sub>D</sub>	34.0	A
TA=70°C	I <sub>D</sub>	34.0	
Pulsed Drain Current B	I <sub>DM</sub>	54.4	
Avalanche Current G	I <sub>AR</sub>	10.9	
Repetitive avalanche energy L=0.1mH G	E <sub>AR</sub>	25.0	mJ
Power Dissipation A TA=25°C	P <sub>D</sub>	46	W
TA=70°C	P <sub>D</sub>	18	
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient A	R <sub>θJA</sub>	13	19	°C/W
Maximum Junction-to-Ambient A Steady State		26	31	°C/W
Maximum Junction-to-Lead c Steady State	R <sub>θJL</sub>	7	12	°C/W

## STATIC PARAMETERS

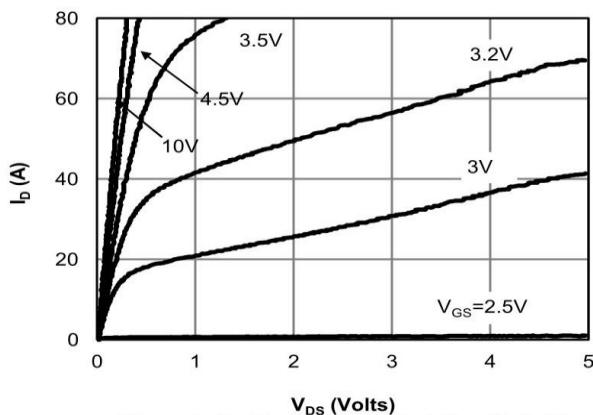
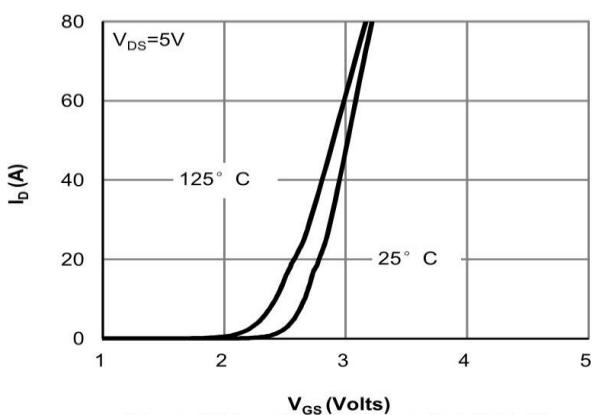
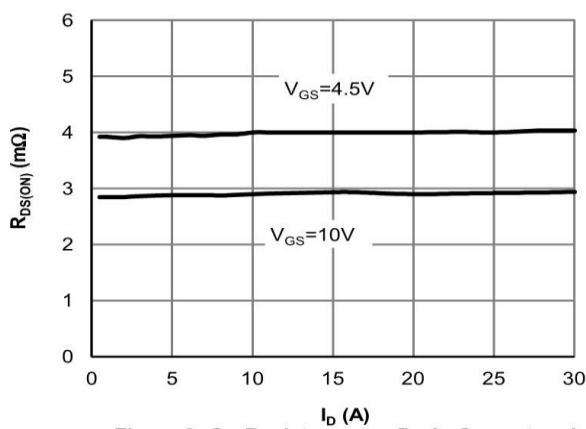
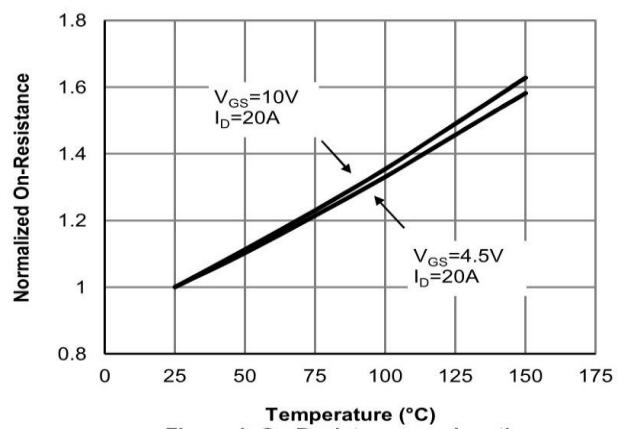
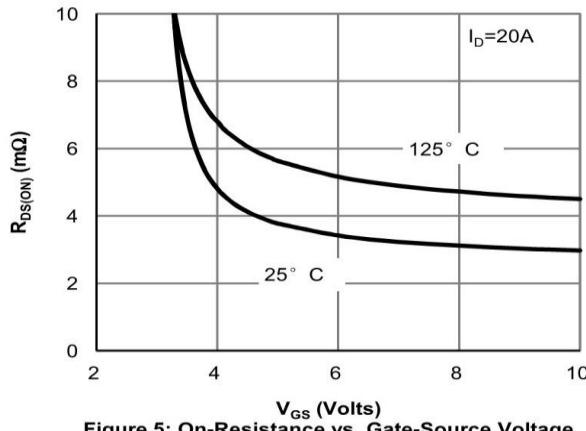
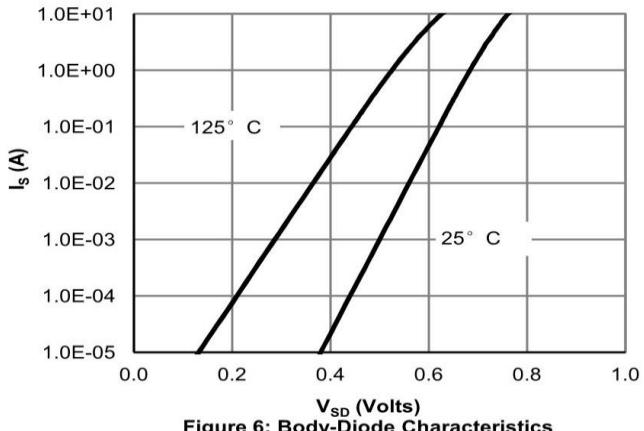
Symbol	Parameter	Conditions	Min	Typ	Max	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D = -250\mu A, V_{GS} = 0V$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	uA
					5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.8	2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$		3.6	5.2	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$		5.7	7.4	
$g_{FS}$	Forward Transconductance	$V_{DS}=5V, I_D=20A$		74		S
$V_{SD}$	Diode Forward Voltage	$I_S=1A, V_{GS}=129V$		0.72	1	V
$I_S$	Maximum Body-Diode Continuous Current				34	A

## DYNAMIC PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$C_{iss}$	Input Capacitance	$V_{GS}=0V, V_{DS}=15V, f=1MHz$		3020	3684	pF
$C_{oss}$	Output Capacitance			330	405	pF
$C_{rss}$	Reverse Transfer Capacitance			280	333	pF
$R_g$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$			5	$\Omega$

## SWITCHING PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$Q_g(10V)$	Total Gate Charge	$V_{GS}=10V, V_{DS}=15V, I_D=20A$		28		nC
$Q_g 4.5V$	Total Gate Charge			14		
$Q_{gs}$	Gate Source Charge			7		
$Q_{gd}$	Gate Drain Charge			10		
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10V, V_{DS}=15V, RL=0.75\Omega, R_{GEN}=3\Omega$		6		ns
$t_r$	Turn-On Rise Time			4.8		
$t_{D(off)}$	Turn-Off DelayTime			16.8		
$t_f$	Turn-Off Fall Time			5.4		
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-8A, dI/dt=500A/\mu s$		12		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=18A, dI/dt=500A/\mu s$		20		nC

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Figure 1: On-Region Characteristics (Note E)**

**Figure 2: Transfer Characteristics (Note E)**

**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**

**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

**Figure 6: Body-Diode Characteristics (Note E)**

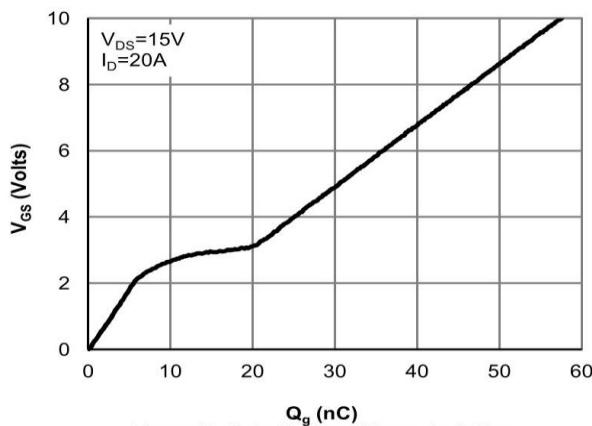
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**


Figure 7: Gate-Charge Characteristics

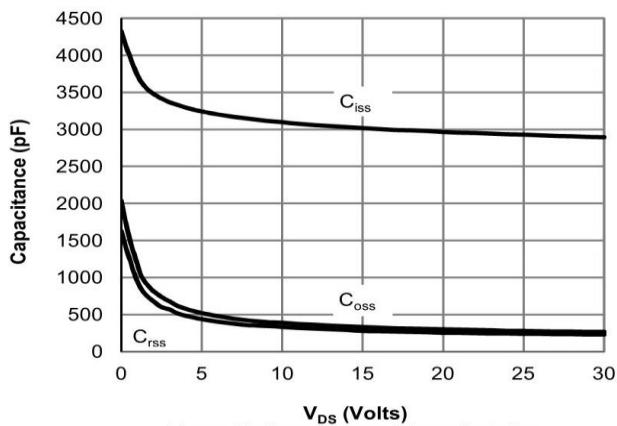


Figure 8: Capacitance Characteristics

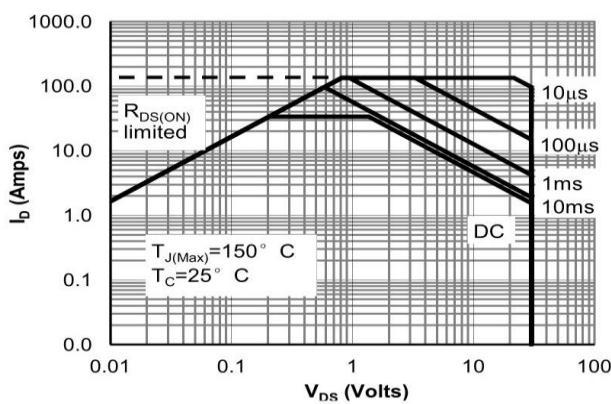


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

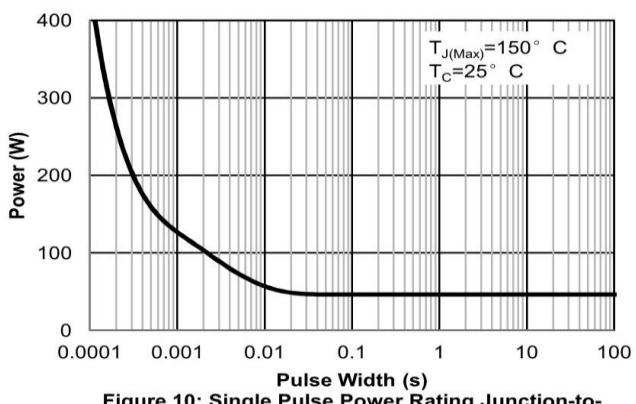


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

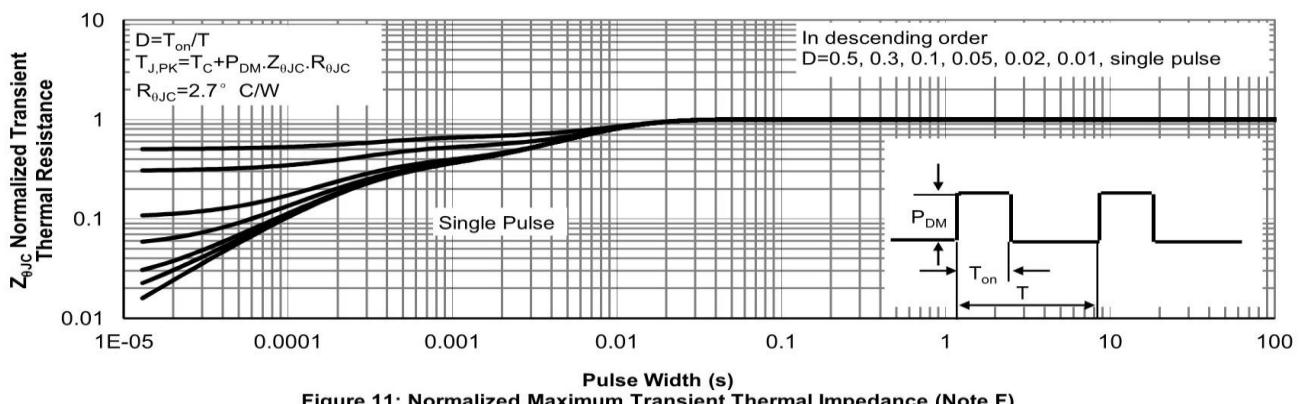


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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